# FAIRCHILD

SEMICONDUCTOR

## **MPS6514**

## **NPN General Purpose Amplifier**

- This device is designed as a general purpose amplifier and switch.
- The useful dynamic range extends to 100mA as a switch and to 100MHz as an amplifier.



1. Emitter 2. Base 3. Collector

## Absolute Maximum Ratings\* Ta=25°C unless otherwise noted

Symbol	Parameter		Value	Units
CEO	Collector-Emitter Voltage		25	V
СВО	Collector-Base Voltage		40	V
ЕВО	Emitter-Base Voltage		4.0	V
)	Collector current	- Continuous	200	mA
J, T <sub>sta</sub>	Junction and Storage Temperature		-55 ~ +150	°C

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

#### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Parameter	Test Condition	Min.	Max.	Units
eristics	÷			
Collector-Emitter Breakdown Voltage	$I_{\rm C} = 0.5 {\rm mA}, I_{\rm B} = 0$	25		V
Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$	40		V
Emitter-Base Breakdown Voltage	$I_{\rm C} = 10\mu {\rm A}, I_{\rm C} = 0$	4.0		V
Collector Cutoff Current	$V_{CE} = 30V, I_E = 0$		50	nA
Collector Cutoff Current	$V_{CB} = 30V, I_E = 0, T = 100^{\circ}C$		1.0	μA
eristics *				
DC Current Gain	I <sub>C</sub> = 2.0mA, V <sub>CE</sub> = 10V	150	300	
	I <sub>C</sub> = 100mA, V <sub>CE</sub> = 10V	90		1
Collector-Emitter Saturation Voltage	I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA		0.5	V
I Characteristics				
Output Capacitance	$V_{CB} = 10V, I_F = 0, f = 100 \text{kHz}$		3.5	pF
	eristics Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cutoff Current Collector Cutoff Current eristics * DC Current Gain Collector-Emitter Saturation Voltage I Characteristics	eristics       I <sub>C</sub> = 0.5mA, I <sub>B</sub> = 0         Collector-Emitter Breakdown Voltage       I <sub>C</sub> = 10 $\mu$ A, I <sub>E</sub> = 0         Emitter-Base Breakdown Voltage       I <sub>C</sub> = 10 $\mu$ A, I <sub>E</sub> = 0         Emitter-Base Breakdown Voltage       I <sub>C</sub> = 10 $\mu$ A, I <sub>C</sub> = 0         Collector Cutoff Current       V <sub>CE</sub> = 30V, I <sub>E</sub> = 0         Collector Cutoff Current       V <sub>CB</sub> = 30V, I <sub>E</sub> = 0, T = 100°C         eristics *       DC Current Gain         I <sub>C</sub> = 100mA, V <sub>CE</sub> = 10V       I <sub>C</sub> = 100mA, V <sub>CE</sub> = 10V         ICollector-Emitter Saturation Voltage       I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA	eristicsCollector-Emitter Breakdown Voltage $I_C = 0.5mA$ , $I_B = 0$ 25Collector-Base Breakdown Voltage $I_C = 10\muA$ , $I_E = 0$ 40Emitter-Base Breakdown Voltage $I_C = 10\muA$ , $I_C = 0$ 4.0Collector Cutoff Current $V_{CE} = 30V$ , $I_E = 0$ 4.0Collector Cutoff Current $V_{CB} = 30V$ , $I_E = 0$ 50Collector Cutoff Current $V_{CB} = 30V$ , $I_E = 0$ , $T = 100^{\circ}C$ 4.0eristics *DC Current Gain $I_C = 2.0mA$ , $V_{CE} = 10V$ 150 $I_C = 100mA$ , $V_{CE} = 10V$ 9010Collector-Emitter Saturation Voltage $I_C = 50mA$ , $I_B = 5.0mA$ 11Characteristics	eristicsCollector-Emitter Breakdown Voltage $I_C = 0.5mA$ , $I_B = 0$ 25Collector-Base Breakdown Voltage $I_C = 10\muA$ , $I_E = 0$ 40Emitter-Base Breakdown Voltage $I_C = 10\muA$ , $I_C = 0$ 4.0Collector Cutoff Current $V_{CE} = 30V$ , $I_E = 0$ 50Collector Cutoff Current $V_{CB} = 30V$ , $I_E = 0$ , $T = 100^{\circ}C$ 1.0eristics *DC Current Gain $I_C = 2.0mA$ , $V_{CE} = 10V$ 150 $I_C = 100mA$ , $V_{CE} = 10V$ 900.5I Characteristics

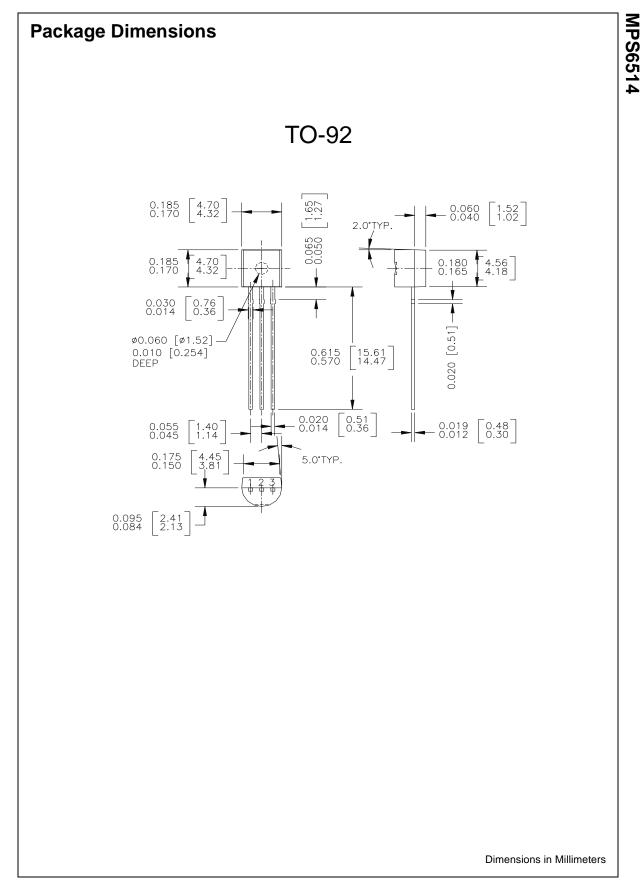
Pulse Test: Pulse Width  $\leq 300 \mu s, \, Duty \, Cycle \leq 2.0\%$ 

## Thermal Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
P <sub>D</sub>	Total Device Dissipation	625	mW
-	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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